MSKSEMI 美森科













ESD

VS

TSS

MOV

GDT

PIFD

MMST3906

Product specification

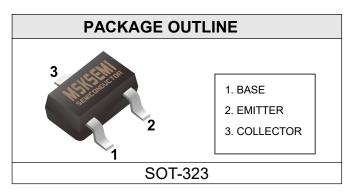




FEATURES

Complementary to MMST3904

Reference News



MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

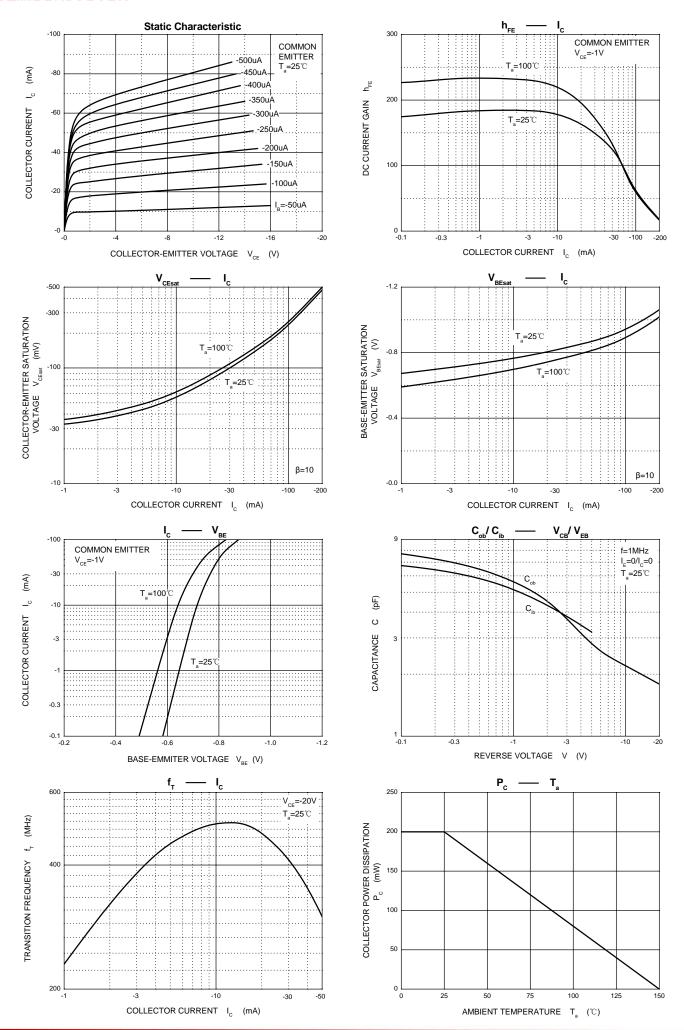
Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-40	V
V _{EBO}	Emitter-Base Voltage	-5	V
lc	Collector Current	-200	mA
Pc	Collector Power Dissipation	200	mW
Roja	Thermal Resistance From Junction To Ambient	625	°C/W
T_J, T_stg	Operation Junction and Storage Temperature Range -55 ~ +15		℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO} *	' I _C =-10μΑ, I _E =0				V
Collector-emitter breakdown voltage	V _{(BR)CEO} *	I _C =-1mA, I _B =0	-40			V
Emitter-base breakdown voltage	V _{(BR)EBO} *	I _E =-10μA, I _C =0	-5			V
Base cut-off current	I _{BL} *	V _{CE} =-30V, V _{EB(Off)} =-3V			-50	nA
Collector cut-off current	Icex*	V _{CE} =-30V, V _{EB(Off)} =-3V			-50	nA
	h _{FE} *	V _{CE} =-1V, I _C =-100μA	60			
DC current gain		V _{CE} =-1V, I _C =-1mA	80			
		V _{CE} =-1V, I _C =-10mA	100		300	
Callegton emitten actumation valtage	V _{CE(sat)} *	I _C =-10mA, I _B =-1mA			-0.2	V
Collector-emitter saturation voltage		I _C =-50mA, I _B =-5mA			-0.3	V
Page emitter caturation voltage	V _{BE(sat)} *	Ic=-10mA, I _B =-1mA	-0.65		-0.85	V
Base-emitter saturation voltage		I _C =-50mA, I _B =-5mA			-0.95	V
Transition frequency f _T V _{CE} =-20V,I _C =-10mA , f=100MH		V _{CE} =-20V,I _C =-10mA , f=100MHz	250			MHz
Collector output capacitance Cob		V _{CB} =-5V, I _E =0, f=1MHz			4.5	pF
Collector output capacitance	C _{ib}	V _{EB} =-0.5V, I _E =0, f=1MHz			10	pF
Delay time	t _d	V _{CC} =-3V, V _{BE(off)} =-0.5V,			35	ns
Rise time	time t _r Ic=-10mA, I _{B1} =-1mA				35	ns
Storage time	ts				225	ns
Fall time	t _f	V _{CC} =3V, I _C =-10mA, I _{B1} = I _{B2} =-1mA			75	ns

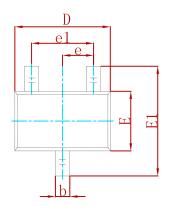
^{*}Pulse test: pulse width ≤300µs,duty cycle≤ 2.0%.

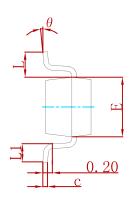


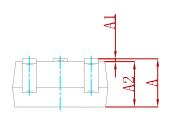




PACKAGEMECHANICALDATA

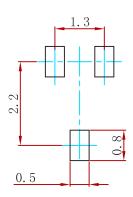






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
E	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026	TYP	
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMST3906	SOT-323	3000



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